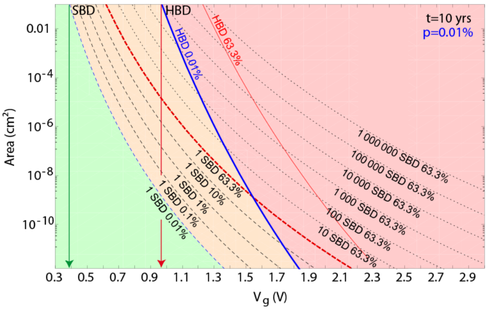

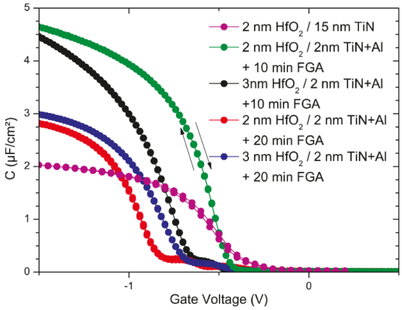

Characterization, integration and reliability of HfO_2 and $LaLuO_3$ high-κ/metal gate stacks for CMOS applications

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Contents

1 Introduction 1

2 High-κ/metal gate stacks for scaled CMOS 3
- 2.1 The Metal-Insulator-Semiconductor (MIS) gate stack 3
  - 2.1.1 Classical MIS capacitance 3
  - 2.1.2 The silicon MOS capacitor 3
  - 2.1.3 From quantum mechanical contribution to Equivalent Oxide Thickness (EOT) 5
  - 2.1.4 Leakage current mechanisms in high-κ gate stacks 6
- 2.2 Scaling of MOSFETs 8
  - 2.2.1 Introduction of high-κ/metal gate stacks 9
- 2.3 Introduction to CMOS Processing 10
  - 2.3.1 Gate-First and Metal-Inserted Poly-Silicon (MIPS) processes 10
  - 2.3.2 Gate-last and replacement gate processes 10

3 Studies of temperature effects in gate stacks 13
- 3.1 Thermodynamic approach 13
  - 3.1.1 Gibbs free energy change and Sanderson's group electronegativity 13
  - 3.1.2 High-κ materials in contact with Si 14
  - 3.1.3 TiN as metal gate on Si/HfO_2 16
  - 3.1.4 TaN as metal gate on Si/HfO_2 17
  - 3.1.5 Increased scavenging by TiN-nanolaminates 19
  - 3.1.6 Summary 22
- 3.2 Spectroscopic study of $LaLuO_3$ gate stack interface reactions 23
  - 3.2.1 X-ray photoemission spectroscopy 23
  - 3.2.2 Hard X-ray photoemission spectroscopy 24
  - 3.2.3 Effective attenuation length in $LaLuO_3$ for hard X-rays 25
  - 3.2.4 Thermal stability of the TiN/$LaLuO_3$ gate stack 31
  - 3.2.5 $LaLuO_3$ integration on Ge 51
  - 3.2.6 Summary 54

3.3 Further EOT scaling concepts 57
  3.3.1 Use of thinner high-κ dielectric 57
  3.3.2 Use of higher-κ dielectrics 57
  3.3.3 Use of thinner SiO_2 interfacial layer 59
  3.3.4 Thin TiN metal gates 62
  3.3.5 Doped TiN 67
  3.3.6 Summary 77

4 Integration of high-κ/metal gate stacks into MOSFETs 79
4.1 Optimization of TiN as gate electrode for the integration with $LaLuO_3$ and HfO_2 79
  4.1.1 Oxygen barrier layers on TiN 83
  4.1.2 Film stress measurements on TiN 86
  4.1.3 Boron penetration and effective work function in MIPS gate stacks with TiN 88
  4.1.4 TiN as metal diffusion barrier 93
  4.1.5 Summary 95
4.2 Device integration of $LaLuO_3$ and HfO_2 96
  4.2.1 Device fabrication 96
  4.2.2 Device results 97
  4.2.3 Summary 104

5 Oxide quality and reliability in high-κ/metal gate stacks 107
5.1 Investigation of oxide traps in high-κ/ metal gate stacks 107
  5.1.1 Introduction to charge-pumping 108
  5.1.2 Device fabrication and data extraction 111
  5.1.3 Impact of interface states on mobility measured by charge pumping 112
  5.1.4 Origin of mobility reduction 117
  5.1.5 Summary 121
5.2 TDDB reliability of advanced FinFET devices 122
  5.2.1 TDDB reliability of HfO_2/TiN on Si-FinFETs 124
  5.2.2 The correct determination of the SBD information 136
  5.2.3 SILC slope for SBD determination in short-channel MOSFETs 136
  5.2.4 Outlook on test time optimization 138
  5.2.5 Summary 148

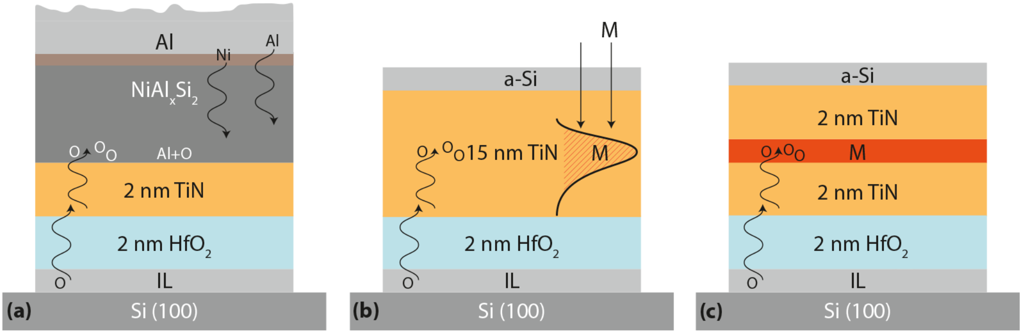
6 Conclusion 153

A MIPS Fabrication Scheme for $LaLuO_3/TiN$ Gate Stacks 155

B Etch-Back Process for SiO_2 159

C Publications 161

D Glossary 165
References 167



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